TECHNICAL DATA DATA SHEET 5311, REV. A

# HERMETIC RAD HARD POWER MOSFET N-CHANNEL QUAD

#### **FEATURES:**

- Four 250 Volt, 0.36 Ohm, 4.4A RAD HARD MOSFETs
- Single Event Effect (SEE) hardened, LET 55, Range: 90µm
  - $\circ$  V<sub>GS</sub> = -15V, V<sub>DS</sub> = 250V
  - $V_{GS} = -20V, V_{DS} = 160V$
- Total Ionization Dose (TID) hardened, 100kRad (Level R)
- Fast Switching
- Low R<sub>DS (on)</sub>
- Pin compatible with IRHQ57214SE, with 1/3<sup>rd</sup> the R<sub>DS(ON)</sub>

## **MAXIMUM RATINGS**

ALL RATINGS ARE AT  $T_c = 25^{\circ}\text{C}$  UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	$V_{GS}$	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I <sub>D</sub>	-	-	4.4	Amps
PULSED DRAIN CURRENT (LIMITED BY T <sub>JMAX</sub> )	I <sub>DM</sub>	-	-	18	Amps
OPERATING AND STORAGE TEMPERATURE	$T_{OP}/T_{STG}$	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	$P_{D}$	-	-	27	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{thJC}$	-	-	4.7	°C/W
AVALANCE ENERGY	E <sub>AS</sub>	-	-	20	mJ

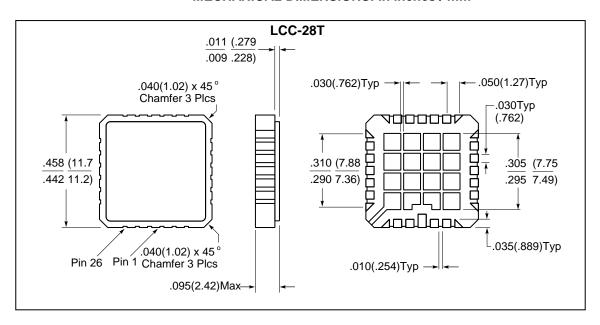
## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV <sub>DSS</sub>	250	295	-	Volts
$V_{GS} = 0V, I_D = 250\mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R <sub>DS(ON)</sub>				Ω
$V_{GS} = 10V, I_{D} = 3A$		-	0.36	0.45	
$V_{GS} = 10V, I_D = 3A, T_A = 125^{\circ}C$		-	-	0.95	
GATE THRESHOLD VOLTAGE $V_{DS} \ge V_{GS}$ , $I_D = 1 \text{mA}$	$V_{GS(th)}$	2.0	3.4	4.0	Volts
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = 200V, V_{GS} = 0V$	I <sub>DSS</sub>	-	-	15	μΑ
$V_{DS} = 200V, V_{GS} = 0V, T_A = 125^{\circ}C$		-	-	250	
GATE TO SOURCE LEAKAGE FORWARD V <sub>GS</sub> = 20V	$I_{GSS}$	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$		-	-	-100	
TURN ON DELAY TIME $V_{DD} = .5V_{DS}$ ,	$t_{d(ON)}$	-	10	14	
RISE TIME $I_D = 3A$ ,	t <sub>r</sub>	-	10	14	nsec
TURN OFF DELAY TIME $R_G = 4.7\Omega$	$t_{d(OFF)}$	-	15	20	
FALL TIME	t <sub>f</sub>	-	11	16	
DIODE FORWARD VOLTAGE $I_S = 4.4A$	$V_{SD}$	-	0.95	1.3	Volts
$V_{GS} = 0V$					
REVERSE RECOVERY TIME $V_{DD} = .5V_{DS}$ ,	t <sub>rr</sub>	-	210	250	nsec
$I_f = 4.4A$					
INPUT CAPACITANCE $V_{GS} = 0 \text{ V}$	$C_{iss}$	-	580	700	_
OUTPUT CAPACITANCE $V_{DS} = 100 \text{ V}$	C <sub>oss</sub>	-	45	60	pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	$C_{rss}$	-	2.3	3	

<sup>\*\*</sup>This product is subject to the International Traffic in Arms Regulations (ITAR), 22 C.F.R. Parts 120 - 130, and may not be exported without the appropriate U.S. Department of State authorization.

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#### **MECHANICAL DIMENSIONS: in Inches / mm**



# **PINOUT TABLE**

QUAD MOSFET LCC-28T	GATE	DRAIN	SOURCE
MOSFET 1	PIN 1	PINS 5, 6	PINS 2, 3
MOSFET 2	PIN 8	PINS 12, 13	PINS 9, 10
MOSFET 3	PIN 15	PINS 19, 20	PINS 16, 17
MOSFET 4	PIN 22	PINS 26, 27	PINS 23, 24

Note: Pins 4, 7, 11, 14, 18, 21, 25 and 28 are Not Connected.

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